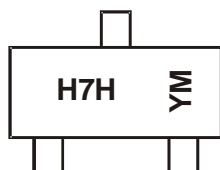


Marking Information



H7H = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021
Code	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
				±40	
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	170	mA
		T _A = +85°C		120	
		T _A = +100°C		105	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	210	mA
		T _A = +85°C		150	
		T _A = +100°C		135	
Maximum Body Diode Forward Current (Note 6)			I _S	0.5	A
				2	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P _D	370	mW
	(Note 6)		510	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	341	°C/W
	(Note 6)		249	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	2.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.0	7.5	Ω	V _{GS} = 5.0V, I _D = 0.05A
Diode Forward Voltage	V _{SD}	—	0.78	1.5	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	26	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	2.8	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.1	—	pF	
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	352	—	pC	V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	203	—		
Gate-Drain Charge	Q _{gd}	—	123	—		
Turn-On Delay Time	t _{D(on)}	—	3.7	—	ns	V _{DD} = 30V, I _D = 0.2A, R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-On Rise Time	t _r	—	2.9	—		
Turn-Off Delay Time	t _{D(off)}	—	8.4	—		
Turn-Off Fall Time	t _f	—	4.7	—		
Body Diode Reverse Recovery Time	t _{rr}	—	9.3	—	ns	I _S = 0.5A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	3.5	—	nC	I _S = 0.5A, dI/dt = 100A/μs

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

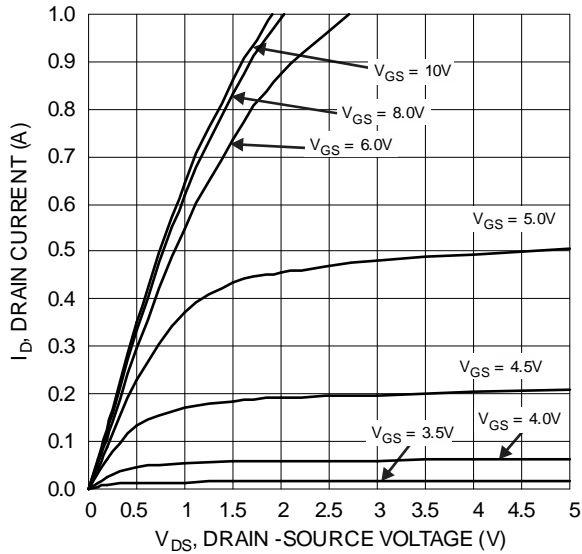


Figure 1 Typical Output Characteristics

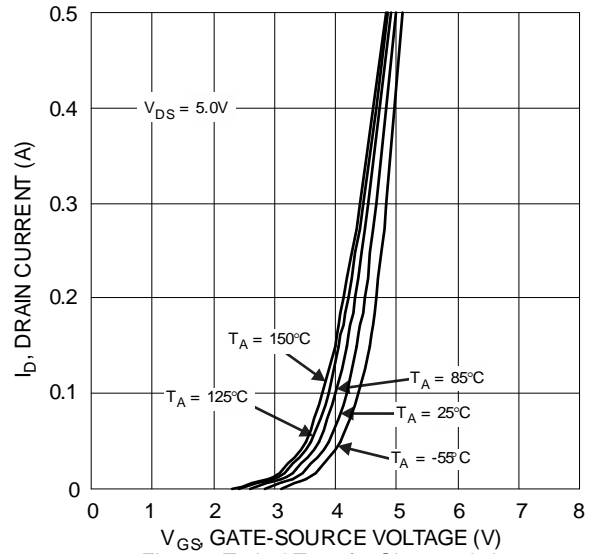


Figure 2 Typical Transfer Characteristics

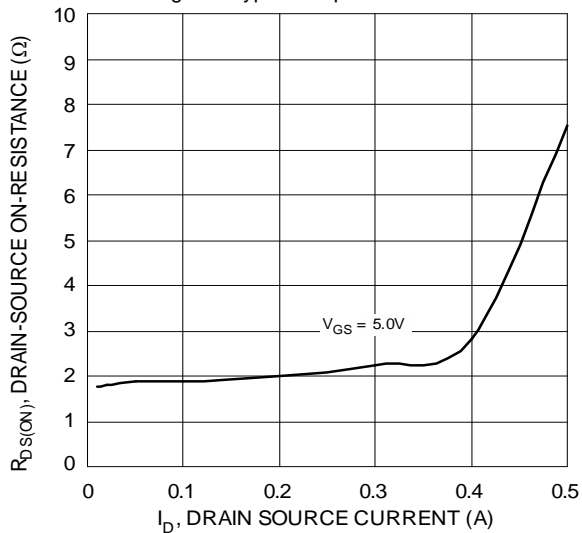


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

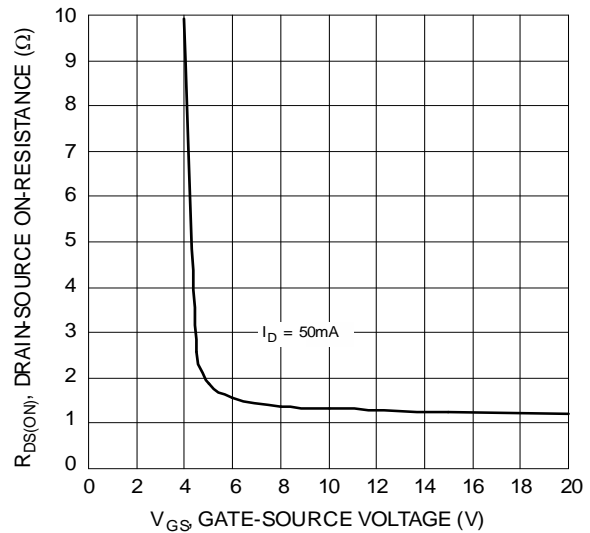


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

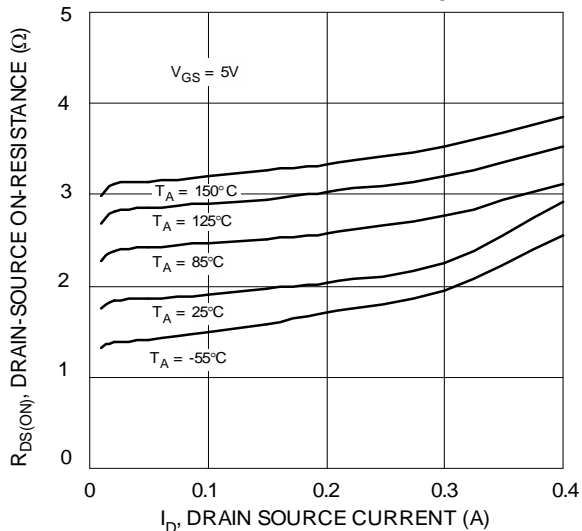


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

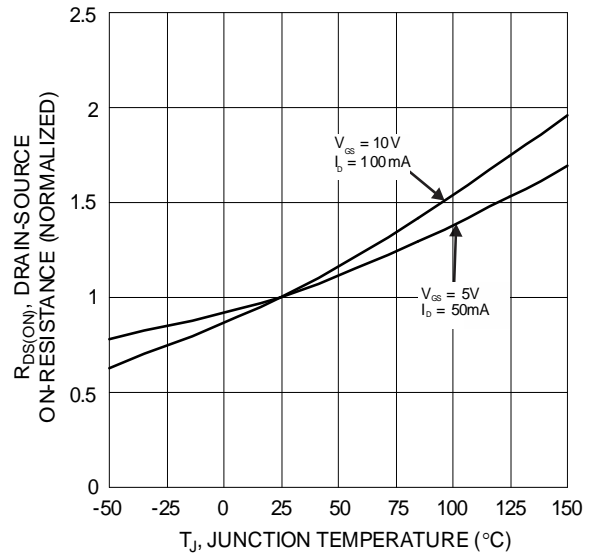
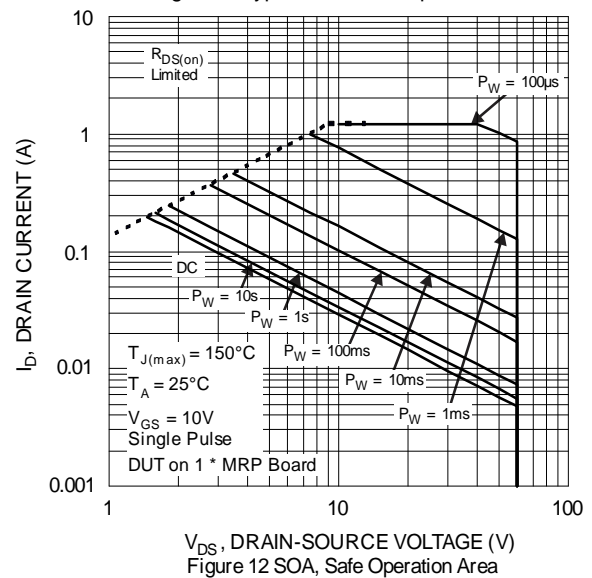
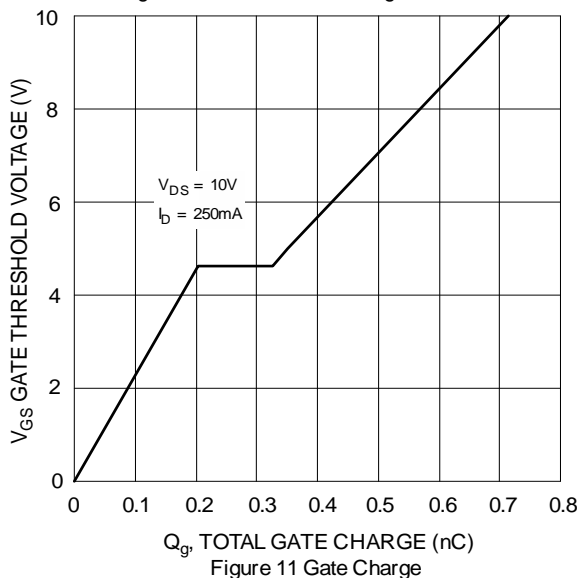
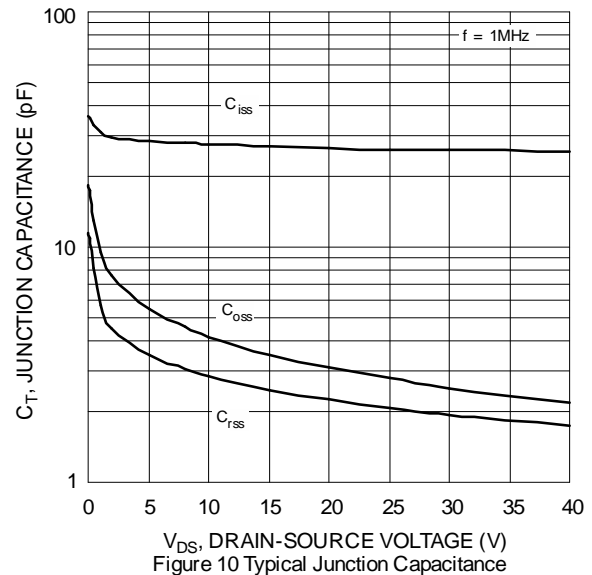
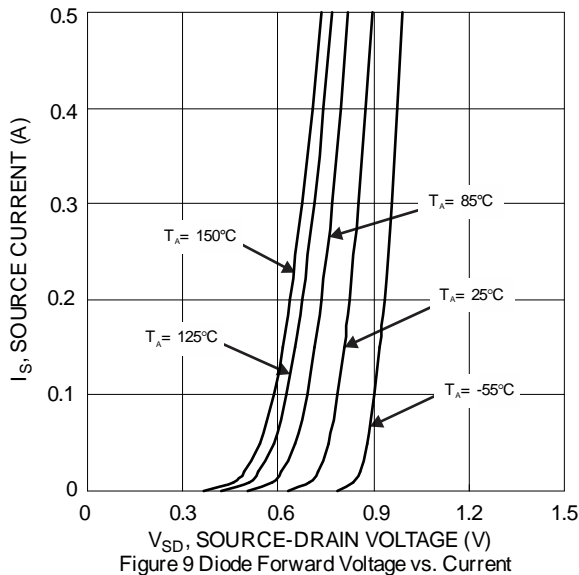
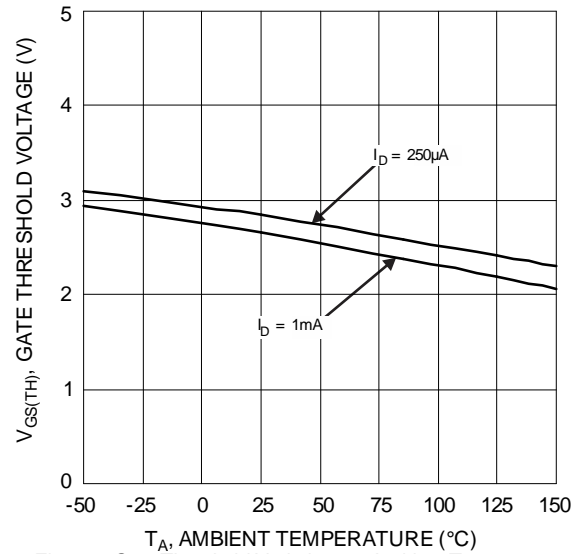
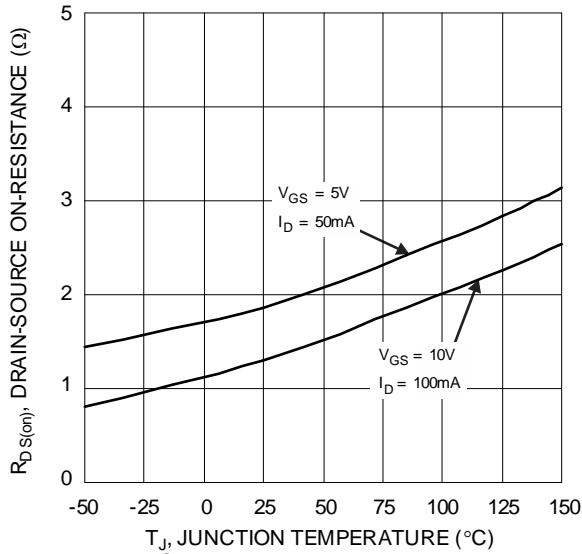
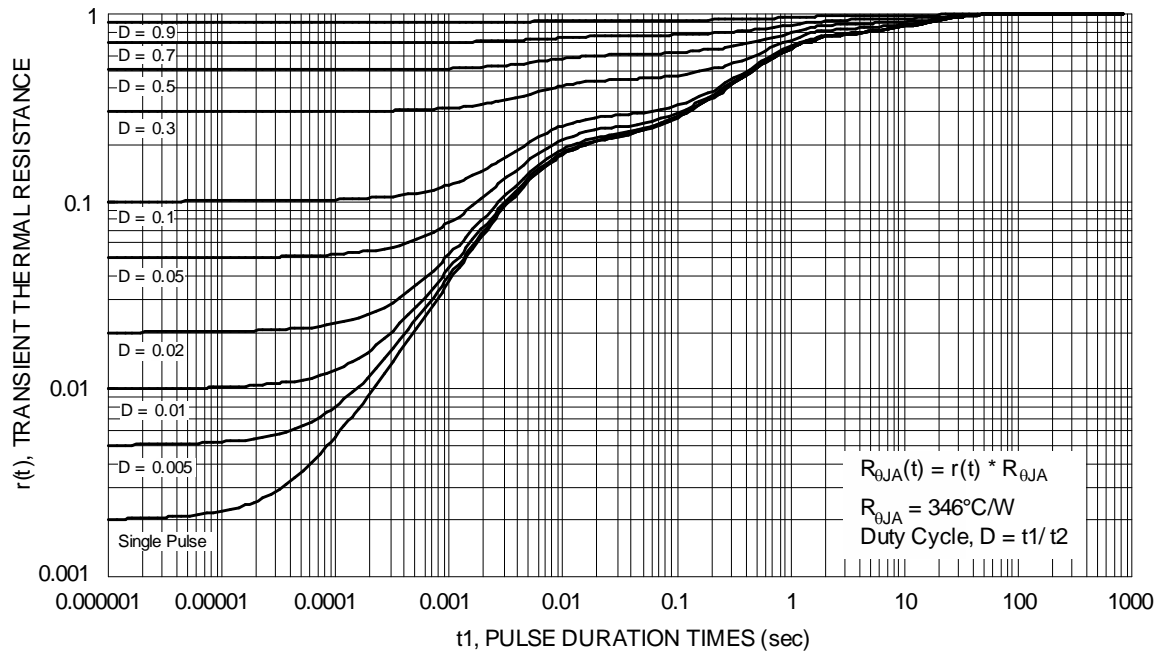


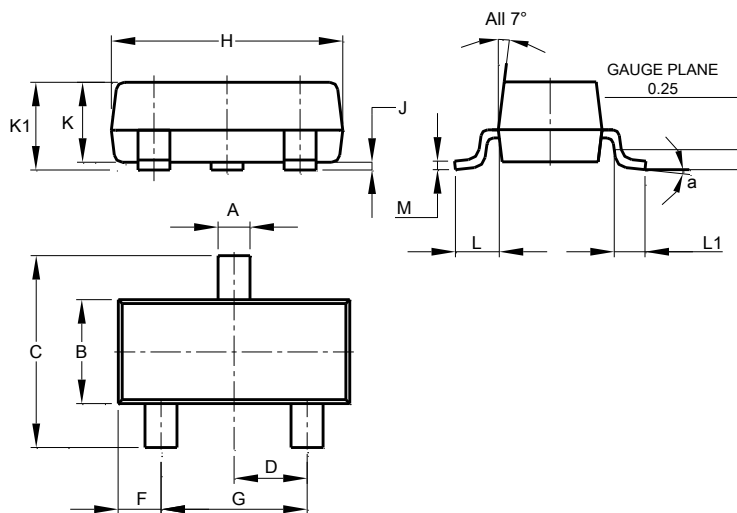
Figure 6 On-Resistance Variation with Temperature





Package Outline Dimensions

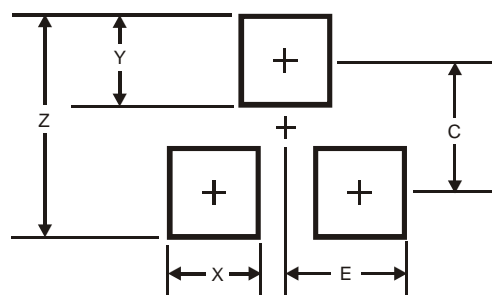
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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